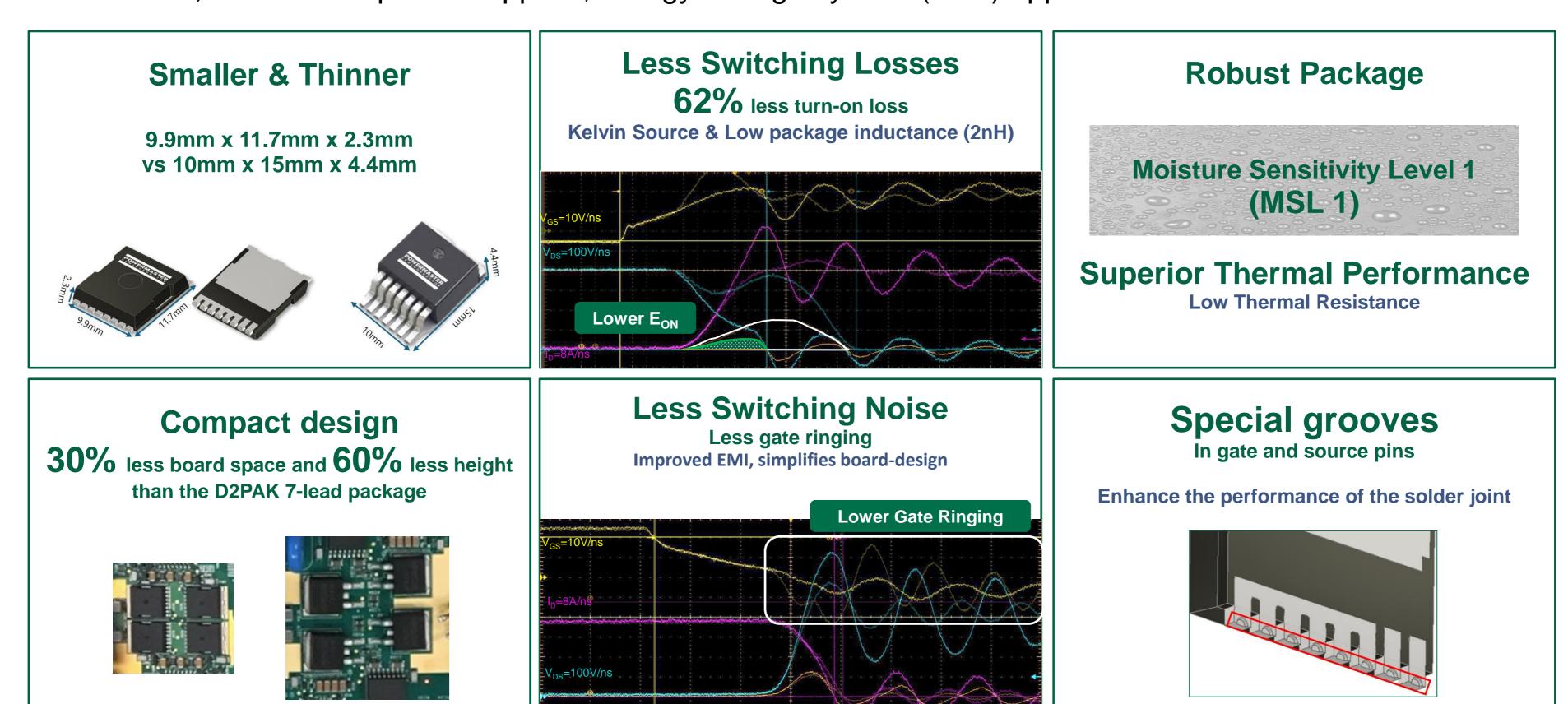


TOLL Package for 650V Gen1 eSiC MOSFET



650V SiC MOSFETs in TO leadless (TOLL) package offer enhanced high power density, efficiency and reliability with improved thermal performance in compact footprint in various power conversion applications such as AI data center, cloud servers, 5G telecom power supplies, energy storage system (ESS) applications.



The TOLL package has a footprint of 9.9mm x 11.7mm, reducing the PCB area by 30% compared to the D2PAK 7-lead package. Moreover, with a thickness of 2.3mm, it has 60% less height than the D2PAK 7-lead package.

The TOLL offers superior thermal performance and low package inductance (2nH) compared to D2PAK 7-lead package. Kelvin source configuration lowers gate noise and reduces turn-on loss by 60% compared to same device without Kelvin source configuration, enabling higher frequency operation and improved power density. The new PCT65N27M1 has a V_{DSS} rating of 650 V with a typical RDS(ON) of 27m Ω and a maximum drain current (I_D) of 84 A.

Power Master Semiconductor's products in TOLL package has special grooves in the gate and source pins to enhance the performance of the solder joint and offers Moisture Sensitivity Level 1 (MSL 1)

650V Gen1 eSiC MOSFET in TOLL Package

Part Name	V_{BR}	R _{DS(ON)}	Package
PCT65N15M1	650V	15mΩ	
PCT65N22M1	650V	22mΩ	
PCT65N27M1	650V	27mΩ	
PCT65N39M1	650V	39mΩ	
PCT65N45M1	650V	45mΩ	

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